

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE0157A2 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

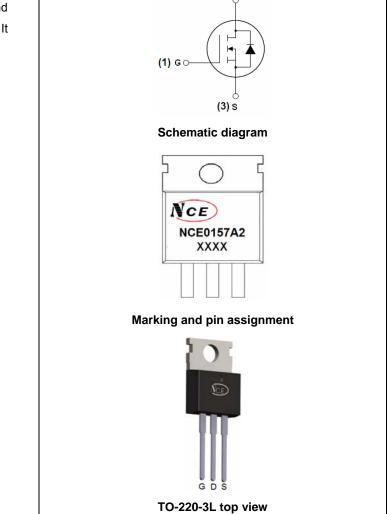
- $V_{DS} = 100V, I_D = 57A$ $R_{DS(ON)} < 17m\Omega @ V_{GS} = 10V$ (Typ:14m Ω)
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



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Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0157A2	NCE0157A2	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	100	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	57	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	40	А
Pulsed Drain Current	I _{DM}	160	А
Maximum Power Dissipation	PD	160	W
Derating factor	-	1.06	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	580	mJ





NCE0157A2

Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{eJC}	0.94	°C/W
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Electrical Characteristics (T_c=25°C unless otherwise noted)

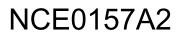
Parameter	Symbol	Symbol Condition		Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100	110	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =28A	-	14	17	mΩ
Forward Transconductance	g fs	V _{DS} =25V,I _D =28A	32	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	3400	-	PF
Output Capacitance	C _{oss}	$V_{DS}=25V, V_{GS}=0V,$	-	260	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	210	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	15	-	nS
Turn-on Rise Time	tr	V _{DD} =30V,I _D =2A,R _L =15Ω	-	11	-	nS
Turn-Off Delay Time	t _{d(off)}	V _{GS} =10V,R _G =2.5Ω	-	52	-	nS
Turn-Off Fall Time	t _f		-	13	-	nS
Total Gate Charge	Qg	N/ 201/1 20A	-	94	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =30V,I _D =30A,	-	16	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	24	-	nC
Drain-Source Diode Characteristics	•					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =28A	-	0.85	1.2	V
Diode Forward Current (Note 2)	Is		-	-	57	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 28A	-	33	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	54	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				

Notes:

- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25 $^\circ \!\! \mathbb{C}, V_{DD}$ =50V,V_G=10V,L=0.5mH,Rg=25 Ω

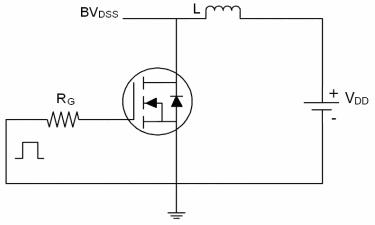




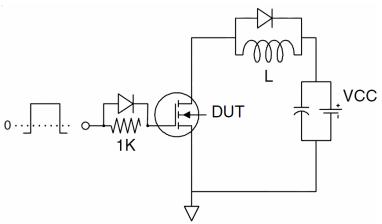


Test Circuit

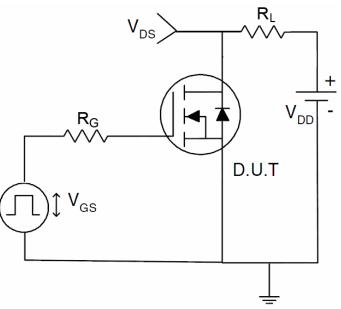




2) Gate charge test Circuit



3) Switch Time Test Circuit



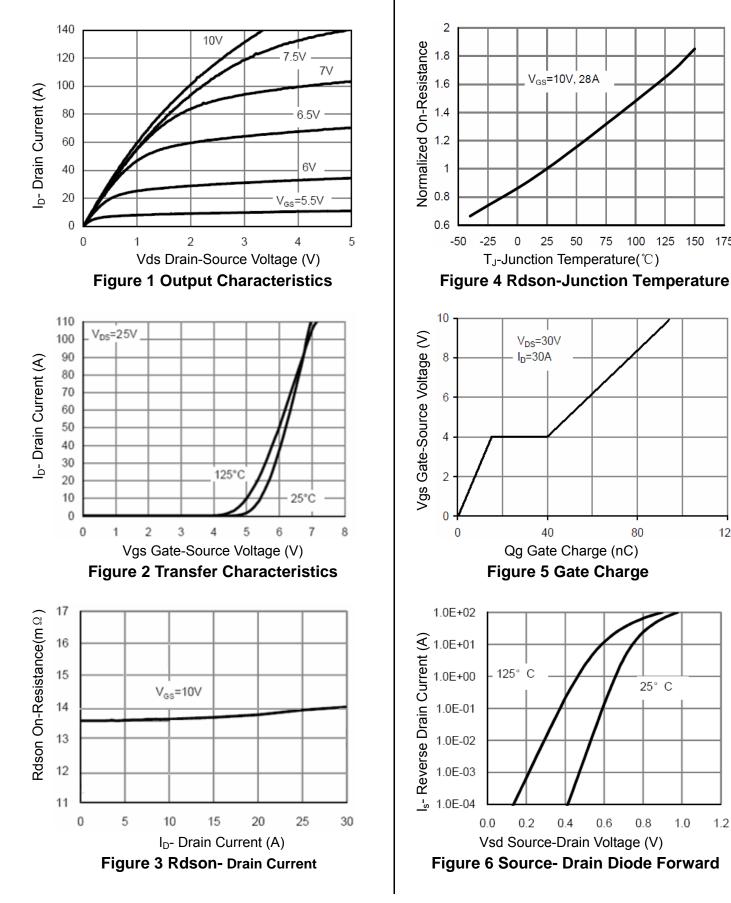




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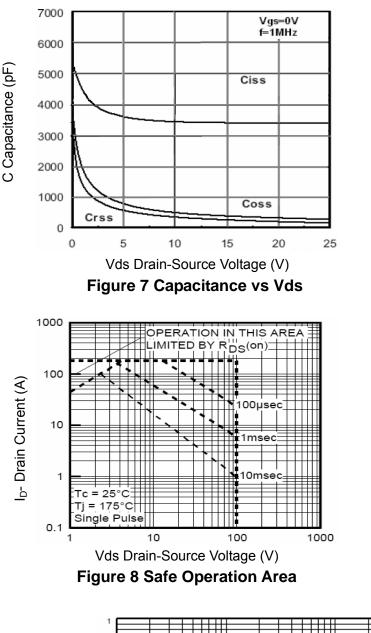
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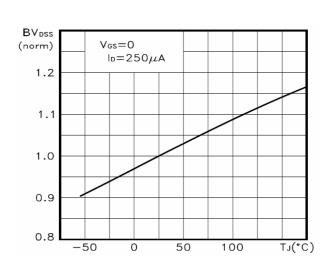
Typical Electrical and Thermal Characteristics (Curves)



1.2







Pb Free Product

NCE0157A2

T_J-Junction Temperature(℃) Figure 9 BV_{DSS} vs Junction Temperature

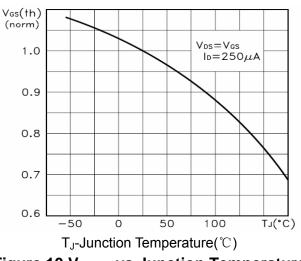


Figure 10 V_{GS(th)} vs Junction Temperature

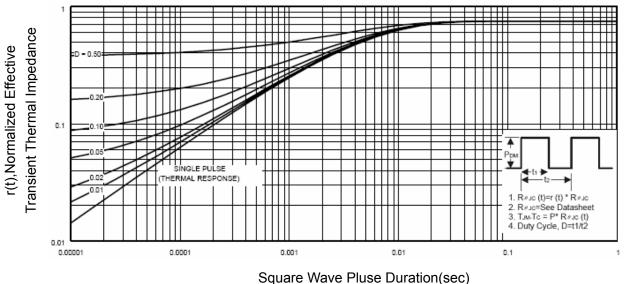
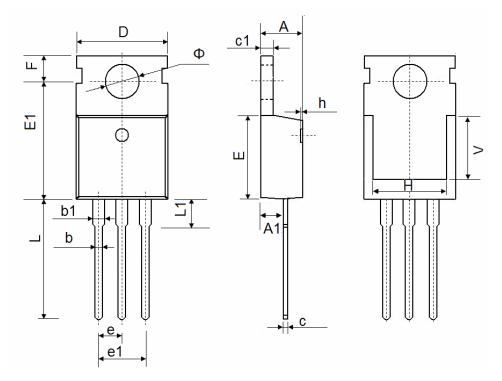


Figure 11 Normalized Maximum Transient Thermal Impedance





TO-220-3L Package Information



Cumula al	Dimensions	In Millimeters	Dimensions In Inches	
Symbol	Min.	Max.	Min.	Max.
А	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
С	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
е	2.540) TYP.	0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
Н	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295	REF.
Ф	3.400	3.800	0.134	0.150





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